IOR HiRel
An Infineon Technologies Company

IRHMB7260
2N7433D4

RADIATION HARDENED POWER MOSFET THRU-HOLE (TABLESS - TO-254AA)

200V, N-CHANNEL
RAD-Hard HEXFET TECHNOLOGY

Product Summary

Part Number	Radiation Level	RDS(on)	I_D
IRHMB7260	100 kRads(Si)	70mΩ	35A*
IRHMB3260	300 kRads(Si)	70mΩ	35A*
IRHMB4260	500 kRads(Si)	70mΩ	35A*
IRHMB8260	1000 kRads(Si)	70mΩ	35A*

TO-254
(TABLESS)

Description

IR HiRel RAD-Hard HEXFET technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low Rdson and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features

- Single Event Effect (SEE) Hardened
- Low RDS(on)
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Electrically Isolated
- Ceramic Eyelets
- Light Weight
- ESD Rating: Class 3B per MIL-STD-750, Method 1020

Absolute Maximum Ratings — Pre-Irradiation

	Parameter		Units
I_D @ V_{GS} = 12V, T_C = 25°C	Continuous Drain Current	35*	A
I_D @ V_{GS} = 12V, T_C = 100°C	Continuous Drain Current	25	
I_{DM}	Pulsed Drain Current ①	140	
P_D @T_C = 25°C	Maximum Power Dissipation	250	W
	Linear Derating Factor	2.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	500	mJ
I_{AR}	Avalanche Current ①	35	A
E_{AR}	Repetitive Avalanche Energy ①	25	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.7	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	9.3 (Typical)	g

* Current is limited by package

For Footnotes, refer to the page 2.

Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.26	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	70	mΩ	V_{GS} = 12V, I_D = 25A ④
		—	—	77		V_{GS} = 12V, I_D = 35A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 1.0mA
Gfs	Forward Transconductance	9.0	—	—	S	V_{DS} = 15V, I_D = 25A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	V_{DS} = 160V, V_{GS} = 0V
		—	—	250		V_{DS} = 160V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -20V
Q_G	Total Gate Charge	—	—	290	nC	I_D = 35A
Q_{GS}	Gate-to-Source Charge	—	—	42		V_{DS} = 100V
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	120		V_{GS} = 12V
$t_{d(on)}$	Turn-On Delay Time	—	—	50	ns	V_{DD} = 100V
tr	Rise Time	—	—	200		I_D = 35A
$t_{d(off)}$	Turn-Off Delay Time	—	—	200		R_G = 2.35Ω
t_f	Fall Time	—	—	130		V_{GS} = 12V
Ls +L_D	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm / 0.25in from package) to Source lead (6mm / 0.25 in from package) with Source wire internally bonded from Source pin to Drain pad
C_{iss}	Input Capacitance	—	5300	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	1200	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	360	—		ƒ = 1.0MHz

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	35*	A	
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	140		
V_{SD}	Diode Forward Voltage	—	—	1.8	V	T_J = 25°C,I_S = 35A, V_{GS} = 0V④
t_{rr}	Reverse Recovery Time	—	—	820	ns	T_J = 25°C, I_F = 35A, V_{DD} ≤ 50V
Q_{rr}	Reverse Recovery Charge	—	—	8.5	μC	di/dt = 100A/μs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

* Current is limited by package

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.5	°C/W
$R_{\theta CS}$	Case -to-Sink	—	0.21	—	
$R_{\theta JA}$	Junction-to-Ambient (Typical socket mount)	—	—	48	

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = 50V, starting T_J = 25°C, L = 0.82mH, Peak I_L = 35A, V_{GS} = 12V

③ I_{SD} ≤ 35A, di/dt ≤ 410A/μs, V_{DD} ≤ 200V, T_J ≤ 150°C

④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%

⑤ **Total Dose Irradiation with V_{GS} Bias.** 12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

⑥ **Total Dose Irradiation with V_{DS} Bias. 160** volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR Hirel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	100 kRads (Si)[1]		300k - 1000 kRads (Si)[2]		Units	Test Conditions
		Min.	Max.	Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	——	200	——	V	V_{GS} = 0V, I_D = 1.0mA
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0	1.25	4.5	V	V_{DS} = V_{GS}, I_D = 1.0mA
I_{GSS}	Gate-to-Source Leakage Forward	——	100	——	100	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	——	-100	——	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	——	25	——	25	µA	V_{DS} = 160V, V_{GS} = 0V
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-3)	——	70	——	110	mΩ	V_{GS} = 12V, I_D = 25A
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-254AA)	——	70	——	110	mΩ	V_{GS} = 12V, I_D = 25A
V_{SD}	Diode Forward Voltage ④	——	1.8	——	1.8	V	V_{GS} = 0V, I_D = 35A

1. Part number IRHMB7260
2. Part numbers IRHMB3260, IRHMB4260 and IRHMB8260

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

Ion	LET (MeV/(mg/cm^2))	Energy (MeV)	Range (µm)	VDS (V)				
				@VGS=0V	@VGS=-5V	@VGS=-10V	@VGS=-15V	@VGS=-20V
Cu	28	285	43	190	180	170	125	——
Br	36.8	305	39	100	100	100	50	——

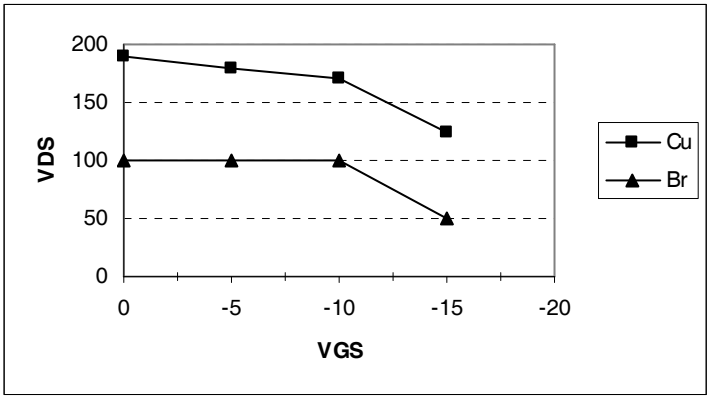


Fig a. Typical Single Event Effect, Safe Operating Area

For Footnotes, refer to the page 2.

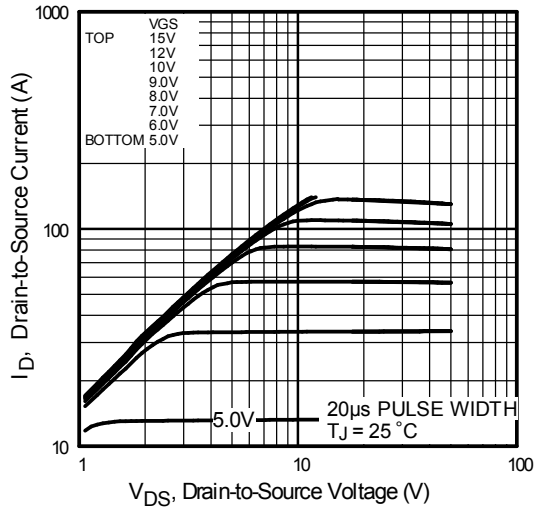


Fig 1. Typical Output Characteristics

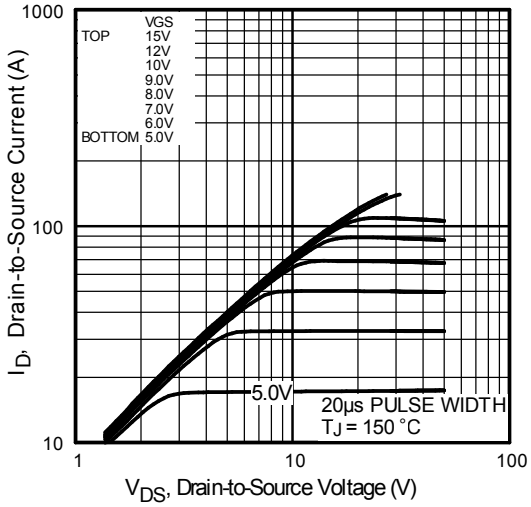


Fig 2. Typical Output Characteristics

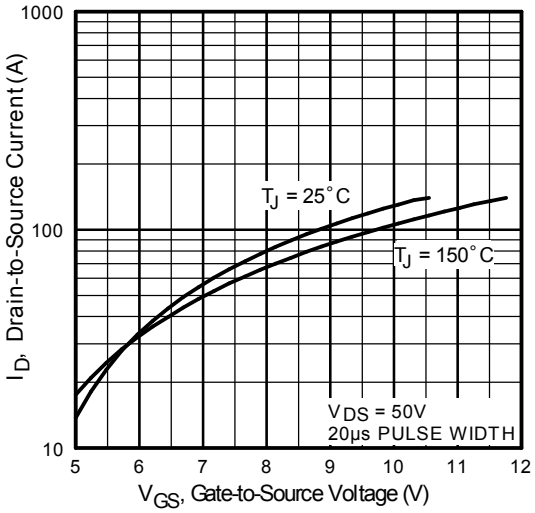


Fig 3. Typical Transfer Characteristics

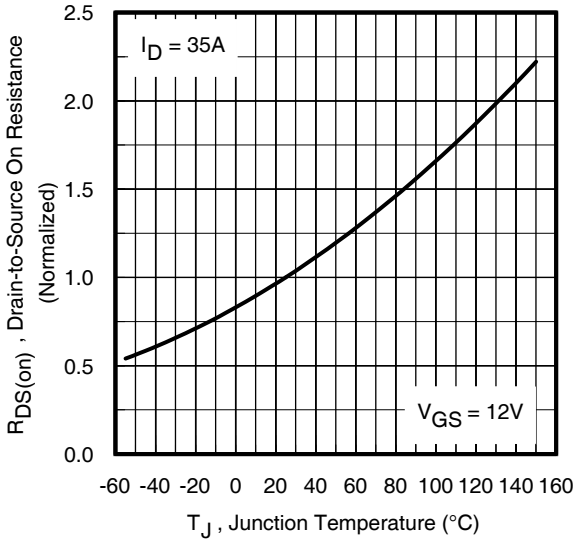


Fig 4. Normalized On-Resistance Vs. Temperature

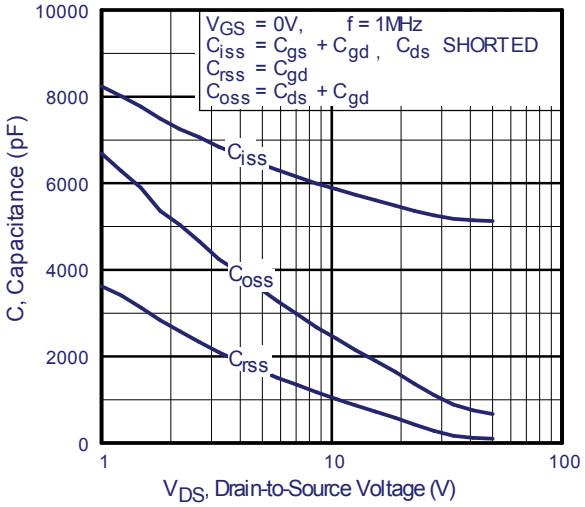


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

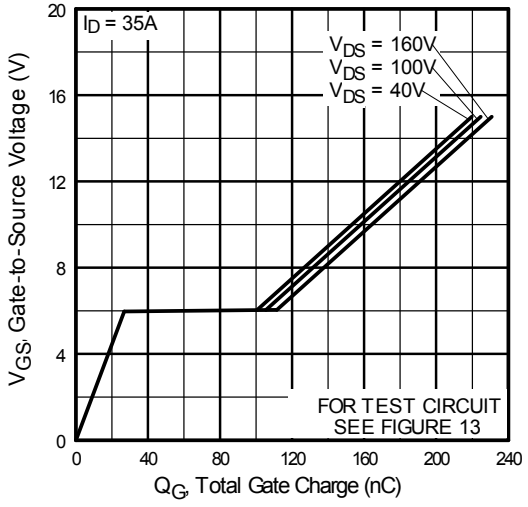


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

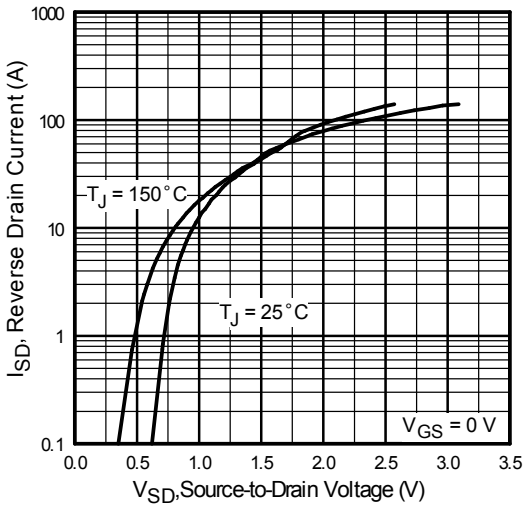


Fig 7. Typical Source-Drain Diode Forward Voltage

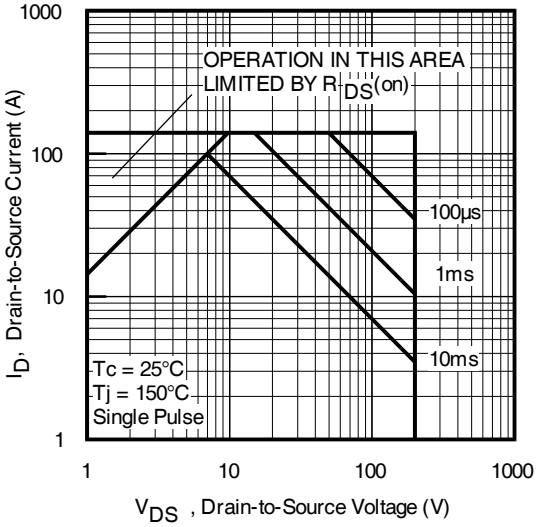


Fig 8. Maximum Safe Operating Area

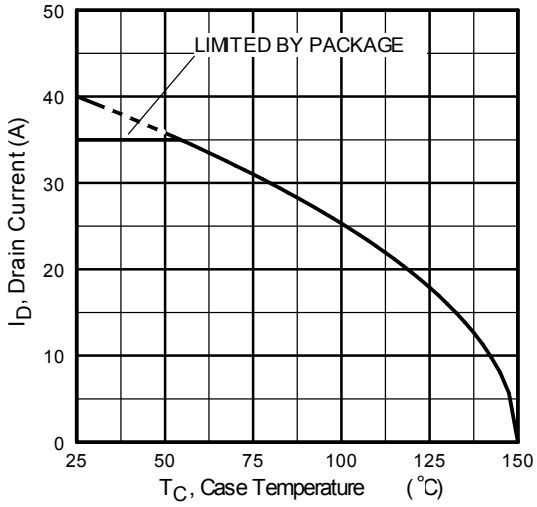


Fig 9. Maximum Drain Current Vs. Case Temperature

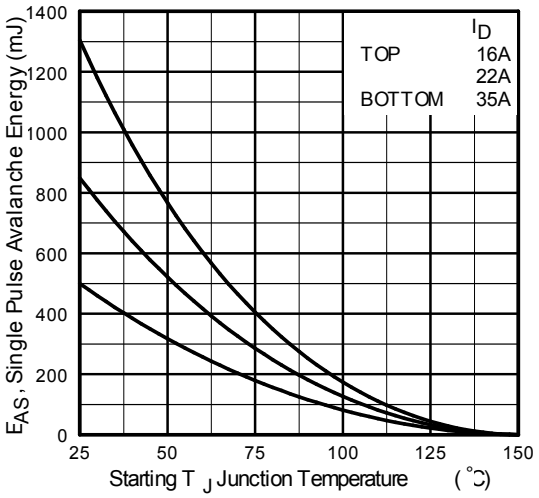


Fig 10. Maximum Avalanche Energy Vs. Drain Current

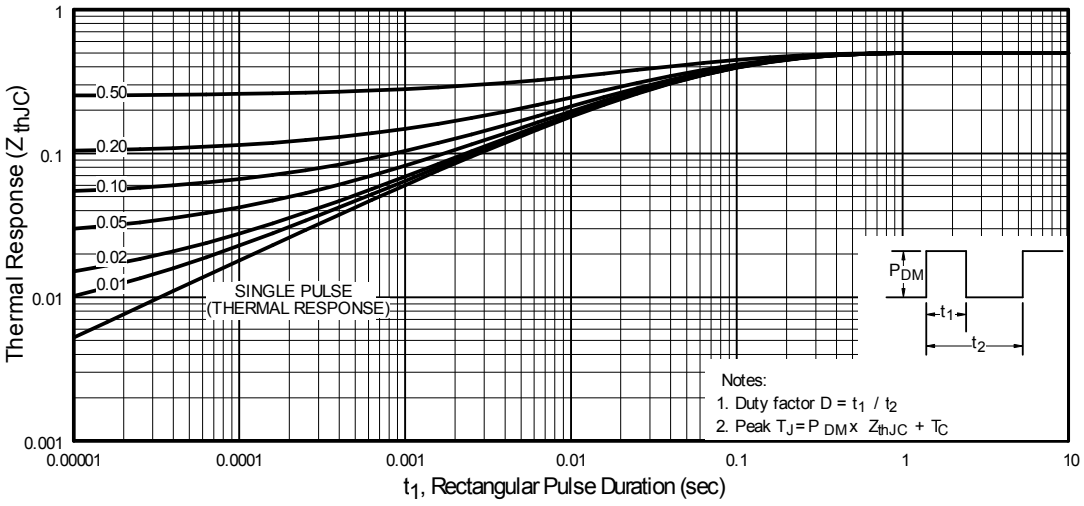


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

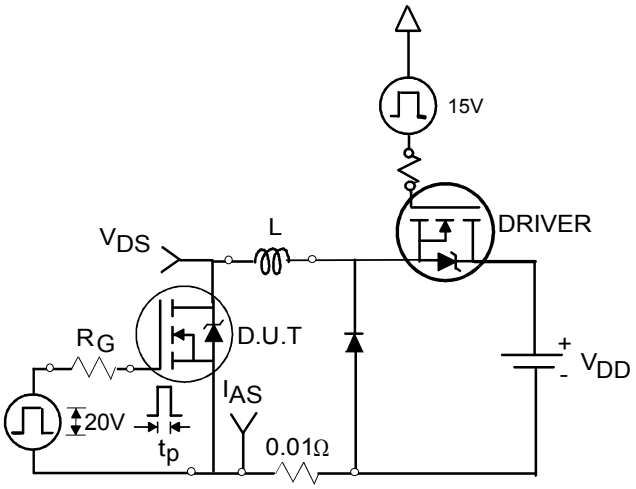


Fig 12a. Unclamped Inductive Test Circuit

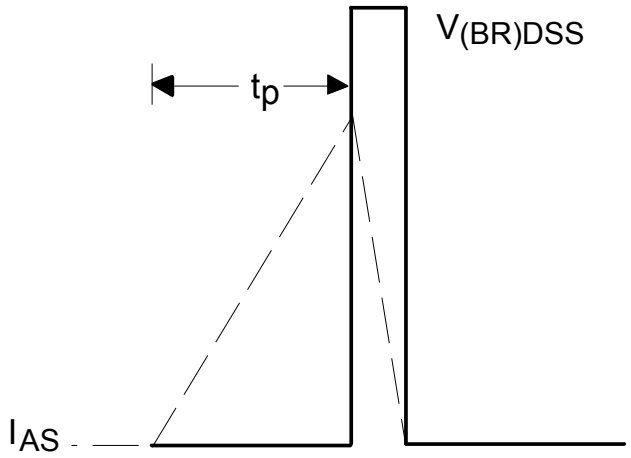


Fig 12b. Unclamped Inductive Waveforms

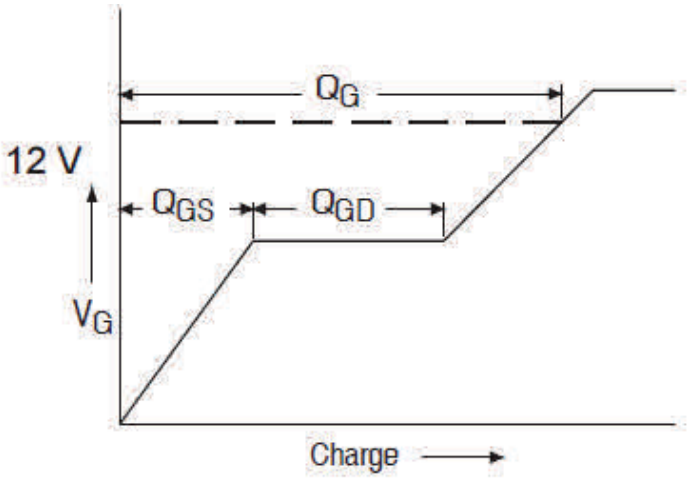


Fig 13a. Gate Charge Waveform

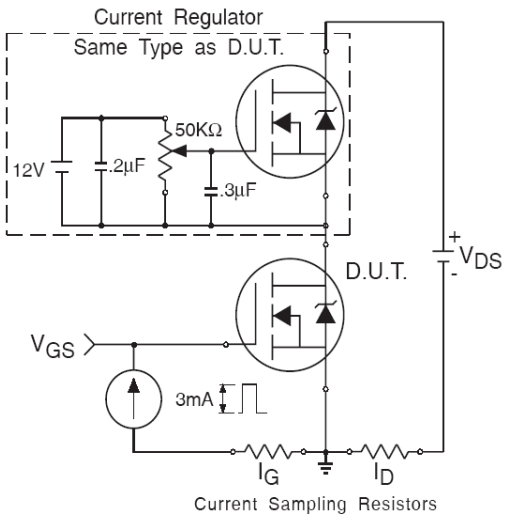


Fig 13b. Gate Charge Test Circuit

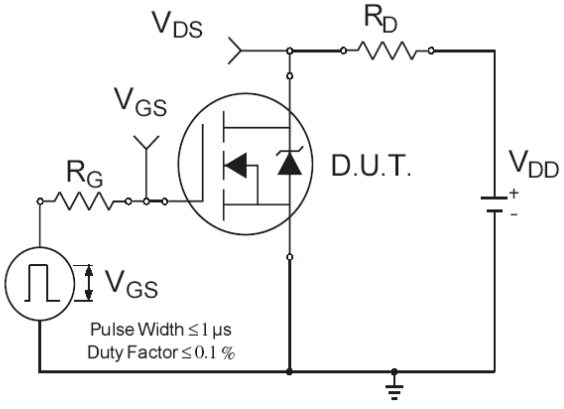


Fig 14a. Switching Time Test Circuit

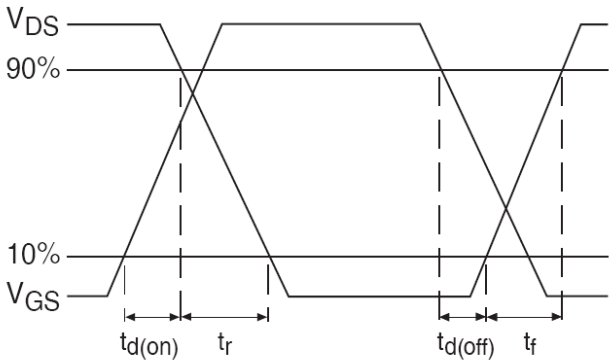
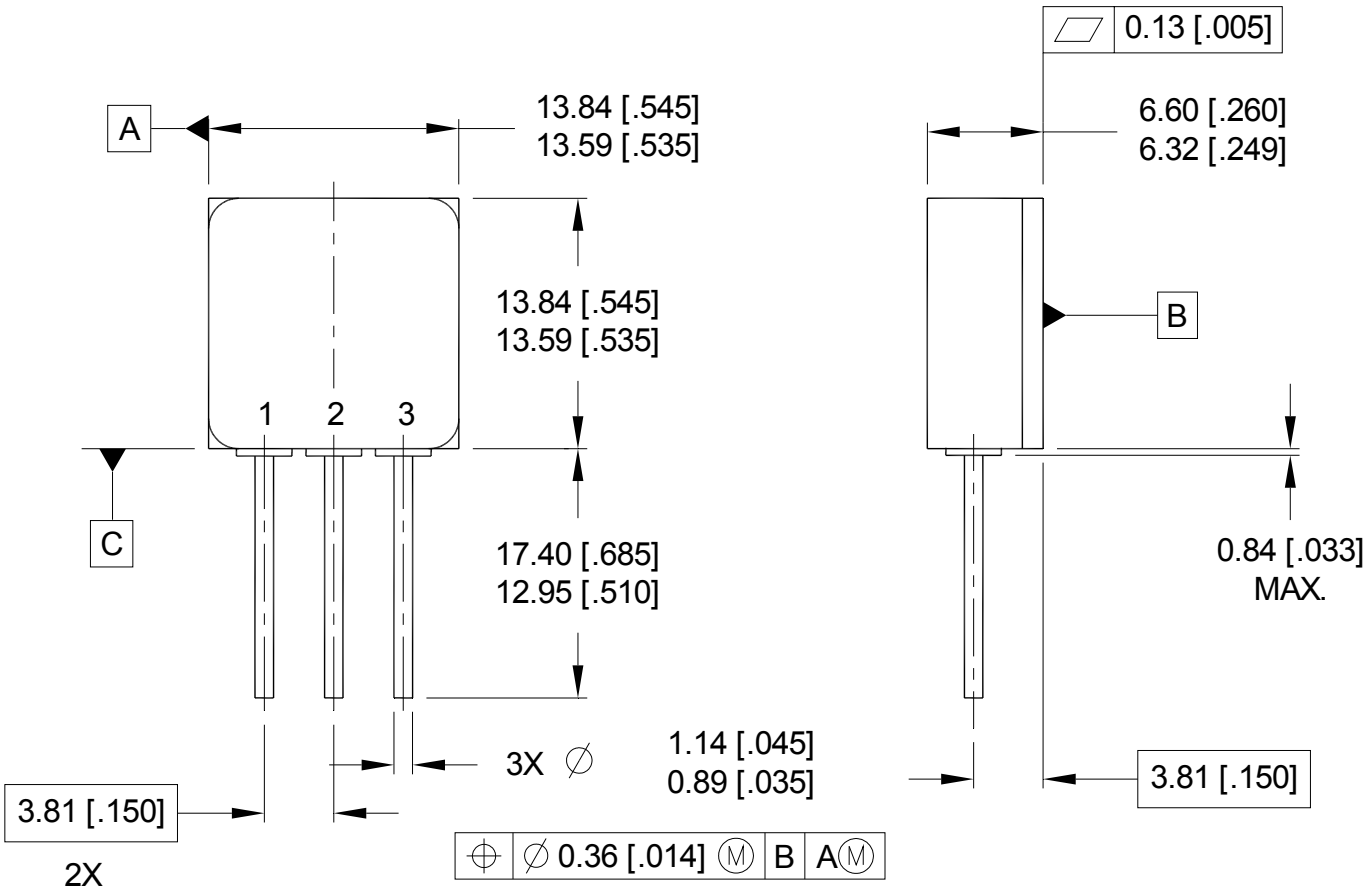


Fig 14b. Switching Time Waveforms

Case Outline and Dimensions — TABLESS - TO-254AA



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: INCH.
4. THIS OUTLINE IS A MODIFIED TO-254AA JEDEC OUTLINE.
5. AVAILABLE WITH EITHER GLASS OR CERAMIC SEALS.

PIN ASSIGNMENTS
1 = DRAIN
2 = SOURCE
3 = GATE

An Infineon Technologies Company

IR HiRel Headquarters: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA Tel: (310) 252-7105
IR HiRel Leominster: 205 Crawford St., Leominster, Massachusetts 01453, USA Tel: (978) 534-5776
IR HiRel San Jose: 2520 Junction Avenue, San Jose, California 95134, USA Tel: (408) 434-5000

Data and specifications subject to change without notice.

IMPORTANT NOTICE

The information given in this document shall be in no event regarded as guarantee of conditions or characteristic. The data contained herein is a characterization of the component based on internal standards and is intended to demonstrate and provide guidance for typical part performance. It will require further evaluation, qualification and analysis to determine suitability in the application environment to confirm compliance to your system requirements.

With respect to any example hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind including without limitation warranties on non- infringement of intellectual property rights and any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's product and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of any customer's technical departments to evaluate the suitability of the product for the intended applications and the completeness of the product information given in this document with respect to applications.

For further information on the product, technology, delivery terms and conditions and prices, please contact your local sales representative or go to (www.infineon.com/hirel).

WARNING

Due to technical requirements products may contain dangerous substances. For information on the types in question, please contact your nearest Infineon Technologies office.

单击下面可查看定价，库存，交付和生命周期等信息

>>Infineon Technologies(英飞凌)